

C1
(concluded)

region of the semiconductor layer 1a. A contact hole 7 for connection to the capacitance line 3b is provided on at least one of the ends of the semiconductor layer 1a extending toward the outside of the gate electrode 3.

IN THE CLAIMS:

Please cancel claims 22-23 without prejudice to or disclaimer of the subject matter contained therein.

Please replace claims 1, 20 and 21 as follows:

C2

1. (Twice Amended) An electro-optical device, comprising:

- a substrate;
- a pixel electrode;
- a scanning line;
- a data line crossing the scanning line; and
- a plurality of transistors disposed correspondingly to intersections between the data line and the scanning line, each of the plurality of transistors including a gate electrode and a semiconductor layer, wherein the semiconductor layer comprises a source region that is connected to the pixel electrode through a contact hole, a drain region that is connected to the data line through a contact hole, a channel region disposed under the gate electrode, and the channel region having a semiconductor portion protruding out of the channel region and not being covered with the gate electrode.

C3

20. (Amended) the electro-optical device according to claim 1, wherein the semiconductor portion protruding in a direction in which the scanning line extends.

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21. (Amended) The electro-optical device according to claim 1, wherein the gate electrode has two parts protruding out of the semiconductor layer, and the source region or the drain region being disposed between the two parts.